

IN THE CLAIMS

Please amend the claims as follows:

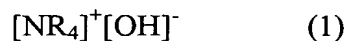
Claims 1-23 (Canceled).

Claim 24 (New): A chemical mechanical polishing process comprising a step of polishing a surface to be polished formed of at least a polysilicon film and/or amorphous silicon film, with an aqueous dispersion obtained by mixing at least a water-soluble quaternary ammonium salt, a basic organic compound other than the water-soluble quaternary ammonium salt, an inorganic acid salt, a water-soluble polymer and abrasive grains into an aqueous medium, wherein a first specific removal rate ratio represented by a ratio of the removal rate of a polysilicon film to the removal rate of a silicon oxide film in the case where the silicon oxide film and the polysilicon film are polished under the same condition, is at least 30.

Claim 25 (New): A chemical mechanical polishing process comprising a step of polishing a surface to be polished formed of at least a polysilicon film and/or amorphous silicon film, with an aqueous dispersion obtained by mixing at least a water-soluble quaternary ammonium salt, a basic organic compound other than the water-soluble quaternary ammonium salt, an inorganic acid salt, a water-soluble polymer and abrasive grains into an aqueous medium, wherein a second specific removal rate ratio represented by a ratio of the removal rate of a polysilicon film to the removal rate of a nitride film in the case where the nitride film and the polysilicon film are polished under the same condition, is at least 50.

Claim 26 (New): The chemical mechanical polishing process according to claim 24, wherein the aqueous dispersion contains the water-soluble quaternary ammonium salt, the basic organic compound other than the water-soluble quaternary ammonium salt, the inorganic acid salt, the water-soluble polymer and the abrasive grains in proportions of 0.005 to 10 % by mass, 0.005 to 10 % by mass, 0.005 to 8 % by mass, 0.001 to 5 % by mass and 0.01 to 10 % by mass, respectively.

Claim 27 (New): The chemical mechanical polishing process according to claim 24, wherein the water-soluble quaternary ammonium salt contained in the aqueous dispersion is a compound represented by the following formula (1):

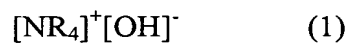


wherein R is an alkyl group having 1 to 4 carbon atoms.

Claim 28 (New): The chemical mechanical polishing process according to claim 24, wherein the inorganic acid salt contained in the aqueous dispersion is an inorganic ammonium salt.

Claim 29 (New): The chemical mechanical polishing process according to claim 25, wherein the aqueous dispersion contains the water-soluble quaternary ammonium salt, the basic organic compound other than the water-soluble quaternary ammonium salt, the inorganic acid salt, the water-soluble polymer and the abrasive grains in proportions of 0.005 to 10 % by mass, 0.005 to 10 % by mass, 0.005 to 8 % by mass, 0.001 to 5 % by mass and 0.01 to 10 % by mass, respectively.

Claim 30 (New): The chemical mechanical polishing process according to claim 25, wherein the water-soluble quaternary ammonium salt contained in the aqueous dispersion is a compound represented by the following formula (1):



wherein R is an alkyl group having 1 to 4 carbon atoms.

Claim 31 (New): The chemical mechanical polishing process according to claim 25, wherein the inorganic acid salt contained in the aqueous dispersion is an inorganic ammonium salt.

DISCUSSION OF THE AMENDMENT

All of the claims have been canceled and replaced with new Claims 24-31. Claims 24 and 25 correspond to Claims 17 and 18, respectively, but presented in independent form. Claims 26-28, and 29-31, are analogous to and supported by Claims 12-14, respectively.

No new matter is believed to have been added by the above amendment. Claims 24-31 are now pending in the application.